The invention refers to the field of electronics and is provided for the manufacture of storage commutation devices, utilized in computer and commutation engineering.

The device contains a base of Pb, onto which there are successively deposited a layer, absorbing the acoustic surface waves, a barrier layer of superconducting ceramics $YBa_2Cu_3O_7$, and a controlling layer of piezocrystal GaAs, in the centre of which it is deposited an anti-pin converter of Cr-Al, between the barrier and the controlling layers being deposited contacts of

Cr-Cu. The contacts of Cr-Cu are placed around the edges of a circumference and consist of longitudinal contacts, placed along the *c* crystallographic axis of the compound $YBa_2Cu_3O_7$, which coincide with the propagation direction of the acoustic surface waves; transversal contacts, placed perpendicular to the crystallographic axis of the compound $YBa_2Cu_3O_7$, which are perpendicular to the propagation direction of the acoustic surface axis; intermediate contacts, placed around the edges of the circumference between the longitudinal and the transversal contacts.